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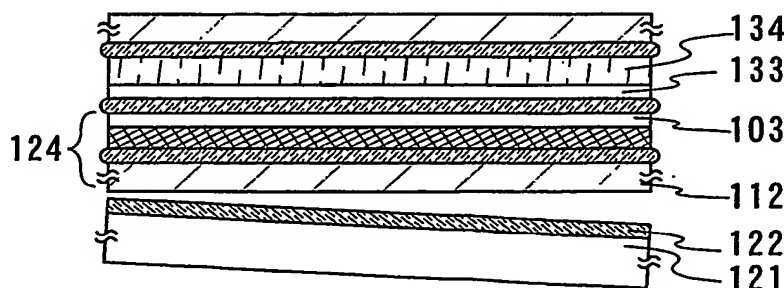
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(54) Title: METHOD OF MANUFACTURING DISPLAY DEVICE



(57) Abstract: To provide a method of
manufacturing a display device having
an excellent impact resistance property
with high yield, in particular, a method
of manufacturing a display device
having an optical film that is formed
using a plastic substrate. The method of
manufacturing a display device includes
the steps of: sequentially forming a
metal film, an oxide film, and an optical
filter on a first substrate; separating
layers including the optical filter from
the first substrate; attaching layers
including the optical filter to a second

substrate; forming a layer including a pixel on a surface of a third substrate; attaching the layer including the pixel to a fourth
substrate; and attaching layers including the optical filter to another surface of the third substrate.

WO 2005/052892 A1